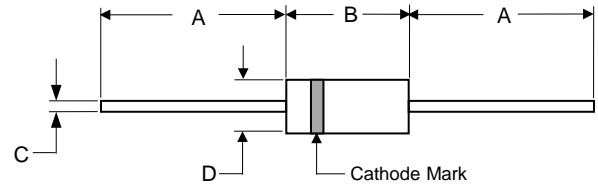


Features

- * High-speed switching
- * This diode is also available in MiniMELF case with the type designation LL4448.



RoHS
COMPLIANT



| DO-35 | | | | |
|-------|--------|-------|-------|------|
| DIM | INCHES | | MM | |
| | MIN | MAX | MIN | MAX |
| A | 1.083 | --- | 27.50 | --- |
| B | --- | 0.154 | --- | 3.90 |
| C | --- | 0.020 | --- | 0.50 |
| D | --- | 0.075 | --- | 1.90 |

Maximum Ratings (T_A=25°C unless otherwise noted)

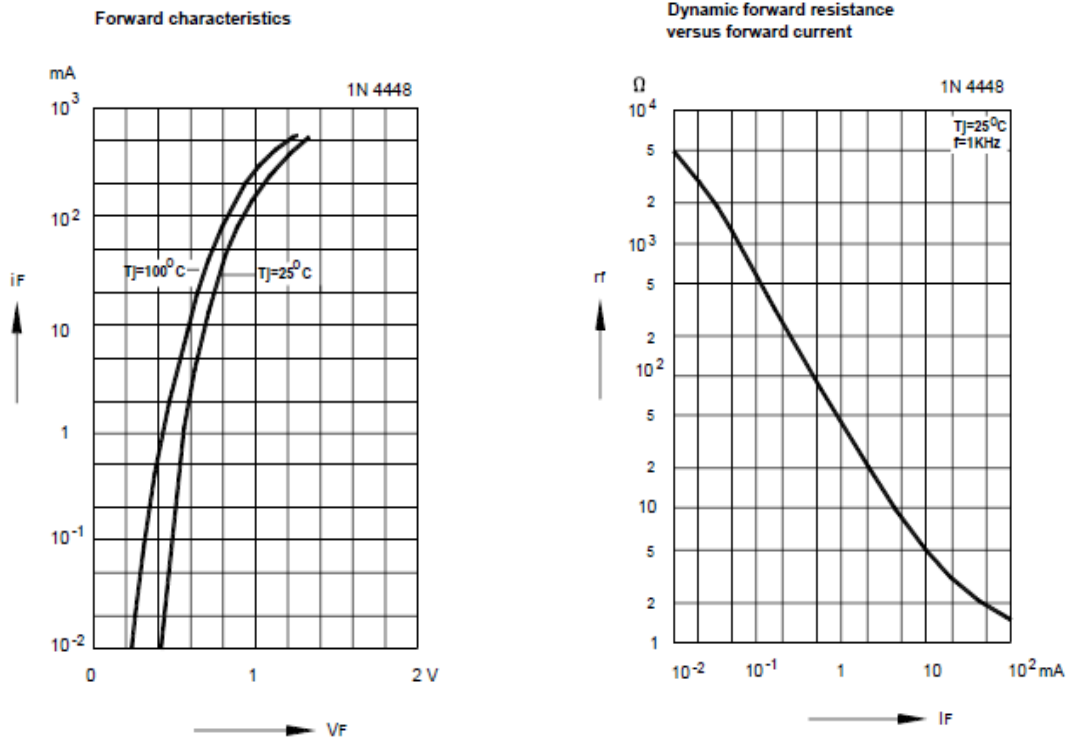
| Parameter | Symbol | Value | Unit |
|------------------------------------|-------------|-------------------|------|
| Peak Reverse Voltage | V_{RM} | 100 | V |
| Reverse Voltage | V_R | 75 | V |
| Average Rectified Forward Current | $I_{F(AV)}$ | 150 | mA |
| Surge Forward Current at $t < 1$ s | I_{FSM} | 500 | mA |
| Power Dissipation | P_{tot} | 500 ¹⁾ | mW |
| Junction Temperature | T_j | 200 | °C |
| Storage Temperature Range | T_{stg} | - 65 to + 200 | °C |

Note: 1) Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

Electrical Characteristics (T_A=25°C unless otherwise noted)

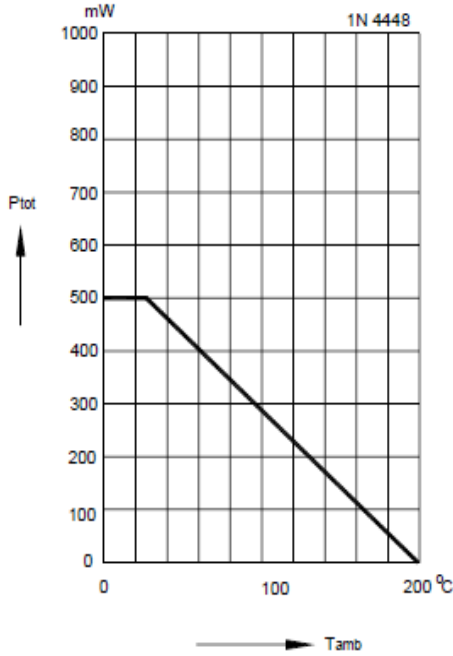
| Parameter | Symbol | Min. | Max. | Unit |
|--------------------------------------------------------------------------------------------------------------------------------------|--------------------|-------------|---------------|----------------|
| Forward Voltage at I _F = 5 mA at I _F = 100 mA | V _F | 0.62 - | 0.72 1 | V |
| Reverse Leakage Current at V _R = 20 V at V _R = 75 V at V _R = 20 V, T _j = 150 °C | I _R | - - - | 25 5 50 | nA μA μA |
| Reverse Breakdown Voltage at I _R = 100 μA | V _{(BR)R} | 100 | - | V |
| Capacitance at V _R = 0, f = 1 MHz | C _{tot} | - | 4 | pF |
| Reverse Recovery Time at I _F = 10 mA to I _R = 1 mA, V _R = 6 V, R _L = 100 Ω | t _{rr} | - | 4 | ns |

Ratings and Characteristic Curves

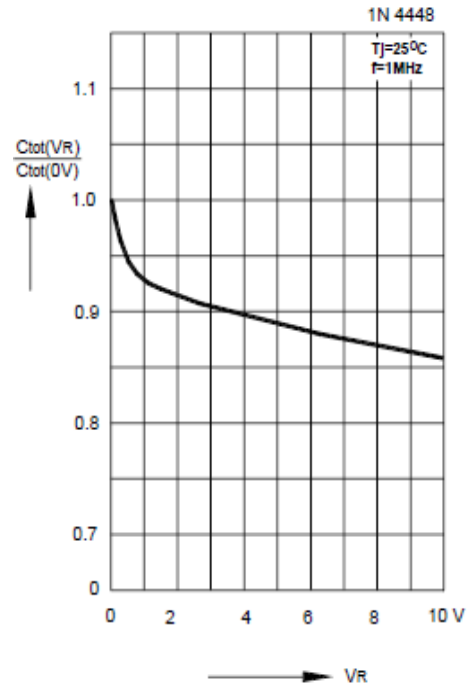


Ratings and Characteristic Curves

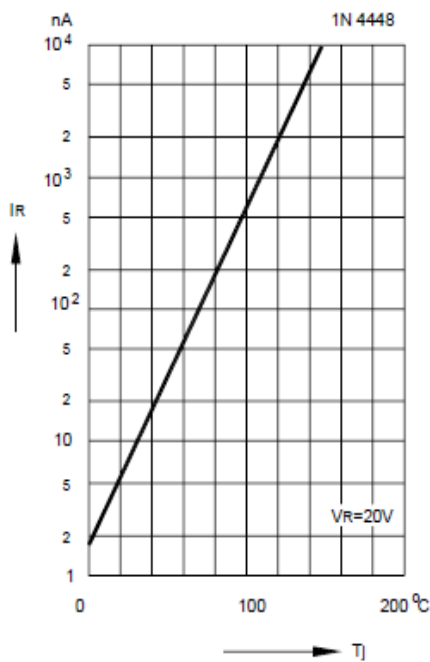
Admissible power dissipation versus ambient temperature
 Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature



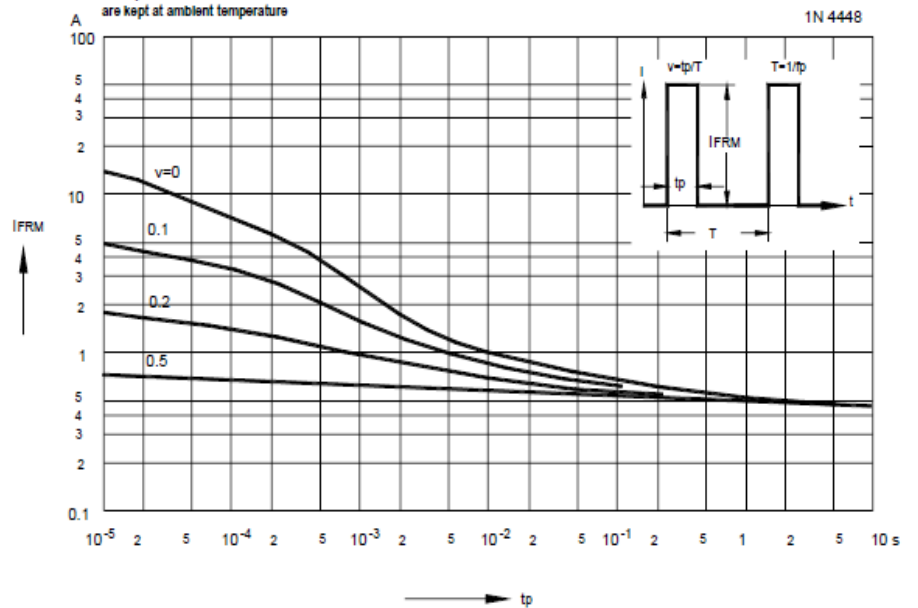
Relative capacitance versus reverse voltage



Leakage current versus junction temperature



Admissible repetitive peak forward current versus pulse duration
 Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature





1N4448
Silicon Epitaxial Planar Switching Diode

Ordering Information

| Part No. | Package | Packing Code | Packing |
|-----------------|----------------|---------------------|----------------|
| 1N4448 | DO-35 | A50 | 5000pcs/Ammo |

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